

REMARKS

II. Response to Office Action

A. Status of the Pending Application

Claims 9-19 and 25-27 are pending in the application. Claims 1-8 and 20-24 are cancelled. Claims 9, 10 and 12-14 stand rejected under 35 U.S.C. § 102(a) as unpatentable over Klose et al. (U.S. Patent No. 6,441,424). Claims 11 and 16-19 are objected to as being dependent upon a rejected base claim.

B. Claim Objections

Claim 12 has been amended to correct the lack of antecedent basis for “whole area of the surface of the depressions.” Claim 14 has been amended to correct the lack of antecedent bases for “whole area of the dielectric layer.” The Examiner is respectfully requested to remove the objections to claims 12 and 14.

Applicant gratefully acknowledges that claims 11, 15 and 16-19 would be allowable if rewritten in independent form and incorporating all of the limitations of the intervening claims.

C. Claim Rejections

Claims 9, 10 and 12-14 are not anticipated under 35 U.S.C. § 102(a) by Klose et al. (U.S. Patent No. 6,441,424). Claim 9 recites, for example and without limitation, a method for fabricating a semiconductor substrate comprising formation of a multiplicity of depressions and a capacitor counterelectrode in a carrier substrate, formation of a dielectric layer at a surface of the depressions and of the carrier substrate, formation and patterning of an electrically conductive layer on the dielectric layer for realizing a multiplicity of capacitor electrodes at least in the multiplicity of depressions, formation of a first insulation partial layer at the processed surface of the carrier substrate, provision of a semiconductor component substrate with a splitting-off boundary layer, and a second insulation partial layer, connection of the semiconductor component substrate and the carrier substrate at their insulating partial layers to form an insulation layer, and

splitting off part of the semiconductor component substrate at the splitting-off boundary layer. The Examiner asserts that Klose et al discloses all the recitations of claim 9. Applicant respectfully disagrees.

Klose et al is directed to an integrated circuit configuration where a capacitor is disposed on a first substrate, and a portion with a contact is disposed on a second substrate. (Klose et al., Abstract). Capacitors are formed in the first substrate in a plurality of depressions. *Id.* Klose et al., however, does not disclose or suggest formation of a first insulation partial layer at the processed surface of the carrier substrate, provision of a semiconductor component substrate with a splitting-off boundary layer, and a second insulation partial layer, or connection of the semiconductor component substrate and the carrier substrate at their insulating partial layers to form an insulation layer, as recited in claim 9.

The Examiner asserts that Klose discloses a first insulation partial layer by referring to layer Sp in Fig. 3 of Klose et al. (See Office Action mailed August 22, 2006, at 2-3). However, the layer Sp is described as a storage node of the formed capacitors, a doped (and therefore conductive) polysilicon layer (Klose et al., Col. 5:65-6:2). The layer referenced by the Examiner as disclosing a first insulation partial layer is conductive and not insulative. In addition, Klose et al. discloses that the layer on the second substrate contacting the first substrate is a contact layer which is gold-plated. (Klose et al., Col. 6, II. 28-30). Klose et al. therefore does not disclose or suggest connection of the semiconductor component substrate and the carrier substrate at their insulating partial layers to form an insulation layer, because Klose et al. requires connection of two conductive surfaces at the connection of the semiconductor component substrate and the carrier substrate.

Accordingly, because Klose et al. does not disclose or suggest all of the recitations of claim 9, Klose et al. does not anticipate claim 9. Applicant therefore respectfully requests the Examiner withdraw the rejection under 35 U.S.C. § 102(a) and solicitation thereof is earnestly solicited.

Claims 10-19 ultimately depend from claim 9, and are therefore patentable for at least the reasons discussed for claim 9 above. Therefore, Applicant respectfully request the Examiner to withdraw the rejections under § 102(a) for claim 9-19.

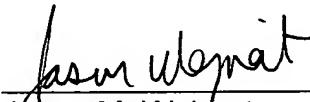
D. Allowable Subject Matter

Applicant gratefully acknowledges that the Examiner has indicated claims 25-27 are allowed.

E. SUMMARY

Pending Claims 9-19 and 25-27 are patentable. Applicant respectfully requests the Examiner grant early allowance of this application. The Examiner is invited to contact the undersigned attorney for the Applicant via telephone if such communication would expedite this application.

Respectfully submitted,



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